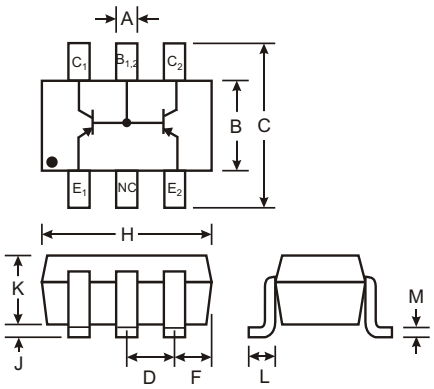
DMMT3906

MATCHED PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Intrinsically Matched PNP Pair (Note 1)
- Small Surface Mount Package
- 2% h_{FE} Matched Tolerance
- **Lead Free/RoHS Compliant (Note 3)**
- **"Green" Device (Note 5 and 6)**



SOT-26			
Dim	**Min**	**Max**	**Typ**
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D			0.95
F			0.55
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
All Dimensions in mm			

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 6. UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking Information - See page 2
- Ordering Information: See Below
- Weight: 0.015 grams (approximate)

Maximum Ratings @ T_A = 25 C unless otherwise specified

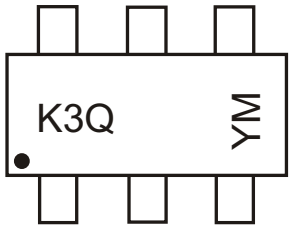
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Power Dissipation (Note 2)	P_d	225	mW
Thermal Resistance, Junction to Ambient (Note 2)	R_{JA}	556	C/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	C

Ordering Information (Note 4 & 6)

Device	Packaging	Shipping
DMMT3906-7-F	SOT-26	3000/Tape & Reel

Notes:
1. Built with adjacent die from a single wafer.
2. Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
3. No purposefully added lead.
4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.
5. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
6. Product manufactured with Date Code 0609 (week 9, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0609 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

Marking Information



K3Q = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: T = 2006
M = Month ex: 9 = September

Date Code Key

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Electrical Characteristics @ T_A = 25 C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40		V	I_C = -10 A, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40		V	I_C = -1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0		V	I_E = -10 A, I_C = 0
Collector Cutoff Current	I_{CEX}		-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -3.0V
Base Cutoff Current	I_{BL}		-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -3.0V
ON CHARACTERISTICS (Note 7)					
DC Current Gain (Note 8)	h_{FE}	60 80 100 60 30	300		I_C = -100µA, V_{CE} = -1.0V I_C = -1.0mA, V_{CE} = -1.0V I_C = -10mA, V_{CE} = -1.0V I_C = -50mA, V_{CE} = -1.0V I_C = -100mA, V_{CE} = -1.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$		-0.25 -0.40	V	I_C = -10mA, I_B = -1.0mA I_C = -50mA, I_B = -5.0mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.65	-0.85 -0.95	V	I_C = -10mA, I_B = -1.0mA I_C = -50mA, I_B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}		4.5	pF	V_{CB} = -5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{ibo}		10	pF	V_{EB} = -0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	2.0	12	k	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.1	10	x 10^{-4}	
Small Signal Current Gain	h_{fe}	100	400		
Output Admittance	h_{oe}	3.0	60	S	
Current Gain-Bandwidth Product	f_T	250		MHz	V_{CE} = -20V, I_C = -10mA, f = 100MHz
Noise Figure	NF		4.0	dB	V_{CE} = -5.0V, I_C = -100 A, R_S = 1.0k f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d		35	ns	V_{CC} = -3.0V, I_C = -10mA, $V_{BE(off)}$ = 0.5V, I_{B1} = -1.0mA
Rise Time	t_r		35	ns	
Storage Time	t_s		225	ns	V_{CC} = -3.0V, I_C = -10mA, I_{B1} = I_{B2} = -1.0mA
Fall Time	t_f		75	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. The DC current gain, h_{FE}, is matched at I_C = -10mA and V_{CE} = -1.0V with typical matched tolerances of 1% and maximum of 2%.

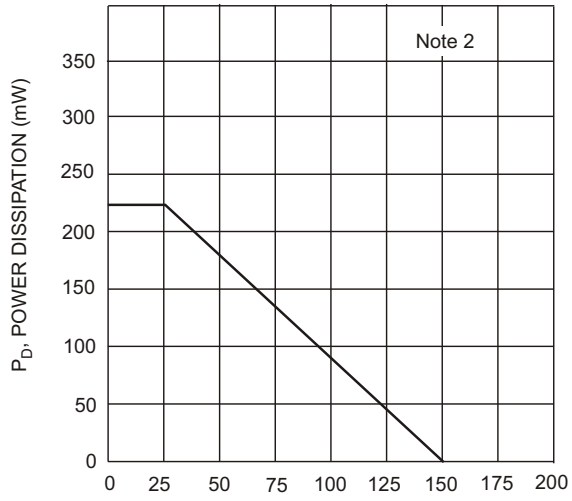


Fig. 1, Max Power Dissipation vs Ambient Temperature, Total Device

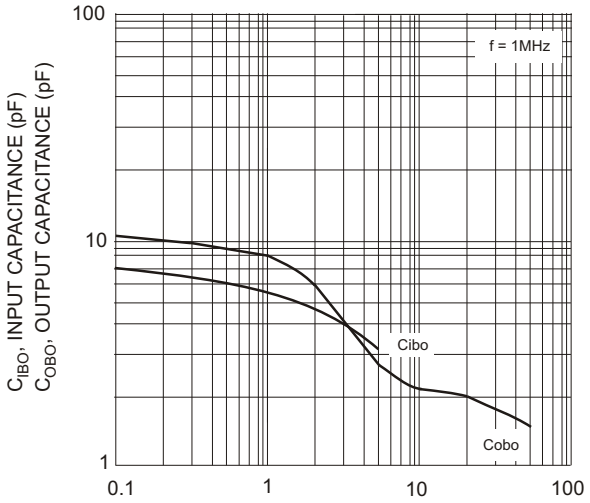


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

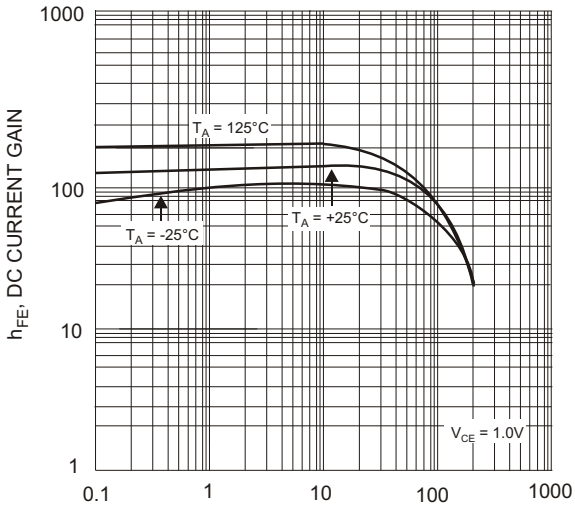


Fig. 3, Typical DC Current Gain vs Collector Current

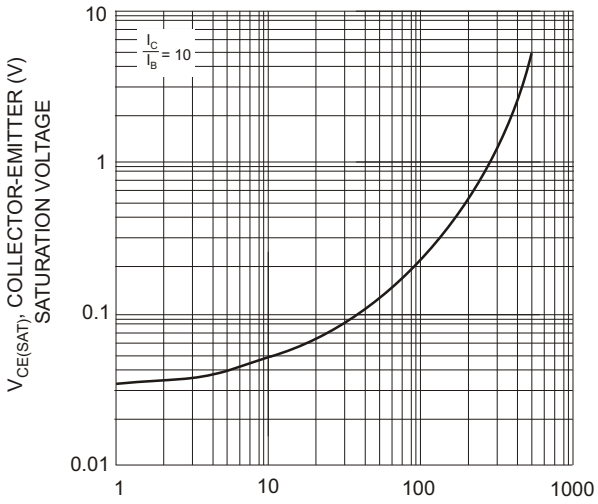


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

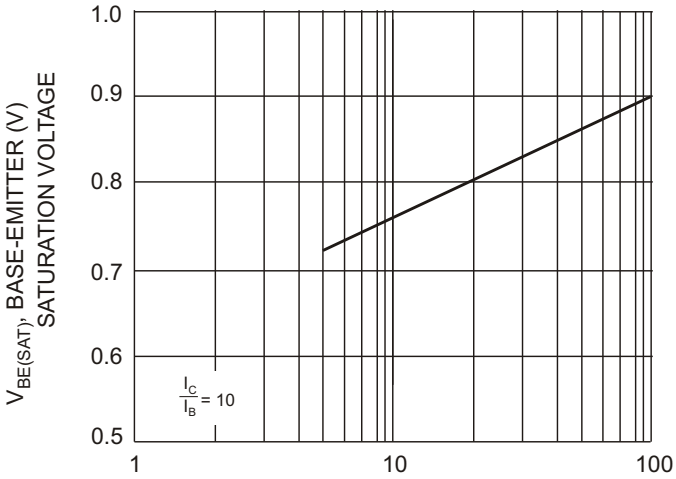


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

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